Densification and phase formation behavior of alumina infiltrated with polycarbosilane

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Conventional powder processing is commonly used to fabricate Al_2O_3/SiC nanocomposites, in which SiC is added in a positive polysilar of tens to hundreds nanometres. Recently a new processing route using a SiC polymeric precursor polysilazane, polysilastyrene, or polycarbosilane has been also attempted, where a polymeric precursor solution is alumina powder. The resulting powder is dried and heat-treated or sintered to form nano-sized SiC particles in single polycarbosilane and sintered at $1600^{\circ}C$ for 2 h in Ar or N_2 . The densification and phase formation behavior was stated was the effect of SiO_2 addition.

Key words: Al₂O₃/SiC nanocomposites, Polycarbosilane, Infiltration, Sintering.

Introduction

It is now well established that the mechanical properties of ceramic materials can be significantly improved by the nanocomposite approach, proposed first by Niihara as a new design concept of structural ceramics [1]. For Al₂O₃, the strength was increased from 350 to 1520 MPa with some increase in toughness and hardness by the addition of only 5 vol% nano-sized SiC particles [1, 2]. Conventional powder processing is commonly used to fabricate the nanocomposites, in which SiC is added in a powder form with sizes of tens to hundreds nanometres. Recently a new processing route using SiC polymeric precursors such as polysilazane, polysilastyrene, or polycarbosilane has been also attempted [3-5]. In this processing, a polymeric precursor solution, prepared with an organic solvent such as toluene or hexane, is mixed with alumina powder. The resulting powder is dried, and then pyrolysis of the added precursor is induced during sintering or separate heat treatment before sintering to form nanosized SiC particles in situ. MoSi₂/SiC nanocomposites prepared using polycarbosilane by hot pressing were reported to exhibit dramatically improved strength both at room and high temperatures in comparison to those prepared by the conventional powder processing [5].

In the present work, porous alumina bodies were

infiltrated with the hexane solution of polycards (PCS) and sintered at 1600°C for 2 h at normal sure. The densification and phase formation were studied with varying sintering conditions atmosphere type (N₂ or Ar) and heating schedule effect of SiO₂ additions was also investigated.

Experimental Procedure

Using an α -Al₂O₃ powder (AES-11, Sumitors Chem Co., Japan), bar-shaped specimens were companies uniaxial pressing (36 MPa, 35 × 8 × 5 mm) and the cold isostatic pressing (200 MPa). For the samples were SiO₂ additions, a SiO₂ sol (Ludox LS, Dupont Wash ington, DE, USA; 30 wt% SiO2, 12 nm) was asset into an alumina slurry and well dispersed to me and wt% SiO2. After drying, bar samples were also pacted. The composition of 2.82 wt% SiOto give 10 wt% mullite after final sintering samples without and with SiO2 are denoted as 400 mm AS, respectively, from now on. The green densities both cases were 59% theoretical density (TD) were used as infiltration bodies after partial single-1200°C for 1 h in air to burn out the organic additional and provide a proper stiffness for the process. The sizes of bars partially sintered $33.8 \times 7.7 \times 4.6$ mm, and the densities measured Archimedes method were 65% TD.

The properties of PCS (NIPUSI Type A. Carbon Co., Japan) used in this study are given in 1. The chemical formula of PCS is [HSCH-According to a previous report [6], its pyrolysis

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Table 1. Properties of polycarbosilane (NIPUSI Type Aa)

Appearance	white powder	
Density (g/cm³)	1.1 (at room temperature)	
Average molecular weight (g/mole)	1400	
Melting point (°C)	230	
Chemical composition (wt%) Si C H O N	50 40 8.1 0.5 0.7	
Ceramic yield after pyrolysis at 1000°C in Ar (wt%) [6]	62 (80.6% SiC, 4.7% SiO ₂ , 12.3% free C)	
Solvent	Hexane, toluene, xylene	

^a Nippon Carbon Co., Japan.

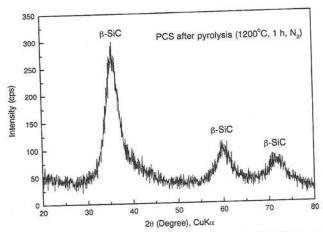


Fig. 1. X-ray diffraction pattern of PCS pyrolysed at 1200° C for 1 h in N_2 .

at 300°C and ends at 800°C, resulting in ceramic materials (62 wt% for the PCS weight) composed of 80.6 wt% SiC, 4.7 wt% SiO₂, and 12.3 wt% free carbon. At 1000°C, it is amorphous, and crystallization to β -SiC begins above 1200°C. Figure 1 shows the XRD pattern of PCS pyrolysed at 1200°C, confirming the crystallization of β -SiC. PCS infiltration solution (20 wt% concentration) was prepared using hexane as a solvent. The partially sintered alumina bars were placed in a flask and evacuated for 5 minutes with a motor-driven aspirator, and then infiltrated with the PCS solution for 30 minutes.

After drying the infiltrated samples completely at room temperature, pyrolysis and sintering were performed with two conditions, PDS and PBS. In the case of the PDS condition, PCS pyrolysis was done during sintering with a hold at 1400°C for 1 h on heating. For the PBS condition, pyrolysis (1400°C, 1 h, N₂ or Ar), followed by an air heat treatment (600°C, 1 h), was done separately prior to sintering. For both the conditions, pressureless sintering was performed in a graphite furnace at 1600°C for 2 h in N₂ or Ar atmosphere.

The air heat treatment was to remove free carbon formed along with SiC during the PCS pyrolysis. The sintering condition, 1600°C and 2 h, was such that the alumina powder (AES 11) can be sintered to 99% TD with no sintering aid. The reason for selecting this condition was to know whether a dense Al₂O₃/SiC nanocomposite can be produced by the PCS infiltration process with the same sintering conditions for monolithic alumina.

Sintered densities were measured by the Archimedes method to find the densification degree of infiltrated samples. The conversion of measured to relative densities was done based on the theoretical densities of the matrices (i.e., 3.98 and 3.88 g/cm3 for AO and AS samples, respectively). This is because their SiC contents were 1.5 vol% so that the theoretical densities calculated using the rule of mixture were of little difference from those of the matrices. In the case of the AS samples, the theoretical density was calculated from the rule of mixtures by assuming the amounts of Al₂O₃ and mullite were 90 and 10 wt%, respectively. Crystalline phase analysis was performed using an Xray diffractometer (XRD) (D/MAX-2000, Rigaku, Japan). Microstructures of the fracture surfaces were observed with a scanning electron microscope (SEM) (JSM 6300, JEOL, Japan).

Results and Discussion

The average amounts of PCS infiltrated in the partially sintered AO and AS bodies were 2.4 wt% after complete drying. The corresponding SiC contents were 1.5 vol% which were calculated from the SiC yield data of PCS pyrolysis in Table 1. The results of sintering and phase analyses of the samples after sintering are summarized in Table 2. The corresponding XRD patterns are given in Figs. 2 and 3. The sintered densities were higher for samples treated in a N₂ atmosphere than for those treated in an Ar atmosphere. The

Table 2. Densities and phases of infiltrated samples after sintering

Sintering condition		Sintered density (%TD ^a)		Crystalline phases besides Al ₂ O ₃	
		AO	AS	AO	AS
N ₂ atmosphere	PDS	92	96	β-SiC 2H-SiC β-Si ₃ N ₄	β-SiC 2H-SiC β-Si ₃ N ₄ 15R-sialon
	PBS	96	96	β-SiC 2H-SiC 15R-sialon	2H-SiC β-Si ₃ N ₄ 15R-sialon
Ar atmosphere	PDS	74	85	β-SiC 2H-SiC	β-SiC 2H-SiC
	PBS	89	89	β-SiC 2H-SiC	β-SiC

^aTheoretical density: 3.98 and 3.88 g/cm³ for AO and AS, respectively.

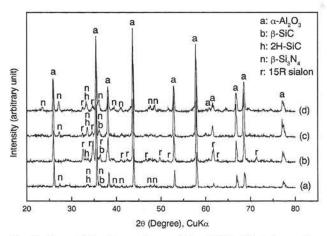


Fig. 2. X-ray diffraction patterns of the PCS infiltrated samples sintered in N_2 atmosphere: (a) AO sample in PDS condition, (b) AO sample in PBS condition, (c) AS sample in PDS condition, and (d) AS sample in PBS condition.

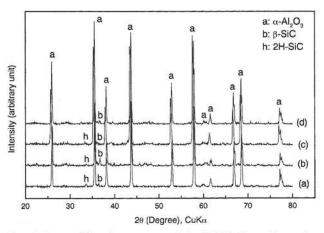


Fig. 3. X-ray diffraction patterns of the PCS infiltrated samples sintered in Ar atmosphere: (a) AO sample in PDS condition, (b) AO sample in PBS condition, (c) AS sample in PDS condition, and (d) AS sample in PBS condition.

PBS condition resulted in higher densification than the PDS condition especially in an Ar atmosphere. Although higher densification was obtained for samples treated in a N₂ atmosphere, β-Si₃N₄ and 15R-sialon (SiAl₄O₂N₄) phases were formed besides the SiC phase (Fig. 2). This indicates that some part of the infiltrated PCS reacted with the N2 atmosphere instead of forming SiC phase, which was not intended. Therefore the higher densification for samples treated in a N2 is attributed to this decreased content of SiC. In ceramic nanocomposites, the SiC particles are known to reduce the sintering rate by inhibiting grain boundary diffusion and grain boundary migration. In the case of samples treated in an Ar atmosphere, only β- and 2H-SiC phases were formed as the secondary phases (Fig. 3). The PBS condition resulted in much higher densification than the PDS condition especially for the AO samples. For the AS samples, the densification in the PDS condition increased significantly to 85%TD, approaching that in the PBS condition speculated that the low densification of the in the PDS condition was due to the management of the pyrolysis products of PCS include and free C (12.3 wt%) besides SiC shown in Table 1. The free carbon can be to form SiC above 1400°C [7, 8] as follows:

$$SiO_2(s) + C(s) = SiO(g) + CO(g)$$

 $SiO(g) + 2C(s) = SiC(s) + CO(g)$
 $\Rightarrow SiO_2(s) + 3C(s) = SiC(s) + 2CO(g)$

In reaction (1), the reaction ratio between \$45-1.7:1 by weight, so that the SiO2 in the PCS means products can be removed by this reaction. However most of the carbon remains and can inhibit some reacting with Al2O3 matrix at higher temperature contrast in the PBS condition, the free carbon and removed by the air heat treatment, resulting in a second densification. The increased densification of the samples in the PDS condition supports the speculation, where the amount of SiO and and enough to react with all the free carbon. It is a that the densification of the PCS infiltrated section 1 be improved by the SiO2 addition or the array treatment. However, the densities obtained are selfprobably for the following reasons. In the case of SiO₂ addition, reaction (1) should be completed reaching temperatures where significant simes are and pores are closed. Otherwise sintering is intering by CO gas evolution. In addition, SiC was a form by this reaction [8-10], which are demonstrated sintering. In the case of the air heat meaning condition used (600°C, 1 h, air) might not be seen to oxidize the free carbon completely it is a second that such problems can be solved with more than control of the heating conditions.

Conclusions

The SiC contents of the PCS infiltrated samples 1.5 vol%. A higher densification was observed samples treated in a N2 atmosphere, but \$-500 15R-sialon (SiAl₄O₂N₄) phases were formed because SiC phase. In the case of samples treated in the atmosphere, only β- and 2H-SiC phases were as the secondary phases as was intended. The cation of the PCS infiltrated samples was proposed the SiO₂ addition or by employing an air hear means step prior to sintering. However, the densities (85 or 89%TD) were still low probably because reactions to remove the free carbon by reduction of SiO₂ and oxidation of carbon seed of siO₂ and oxidation of carbon seed or siO₂ and oxidation seed oxidatio PCS pyrolysis products) were not precisely assets The densification problem will be overcome rigorous control of the heating conditions.

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